

Amendments to the Abstract

Please replace the paragraph at page 9, lines 3 through 25 with the following amended paragraph:

A circuit which accurately controls the word line (pass transistor gate) driving voltage to a voltage which is both controlled and is not significantly greater than is needed to drive the word line. The ~~elements of the present invention~~ circuit eliminates the need for a double-boot-strapping circuit, and ensures that no voltages exceed that necessary to fully turn on a memory cell access transistor. Accordingly, voltage Voltages in excess of that which would reduce reliability are avoided, and accurate driving voltages are obtained. A DRAM is comprised of includes word lines, memory cells having enable inputs connected to the word lines, apparatus ~~for a gate~~ receiving word line selecting signals at first logic levels V_{ss} and V_{dd} , and for providing a select signal at levels V_{ss} and V_{dd} , a high voltage supply source V_{pp} which is higher in voltage than V_{dd} , a circuit for translating the select signals at levels V_{ss} and V_{dd} to levels V_{ss} and V_{pp} and for applying it directly to the word lines ~~for application to the enable inputs~~ whereby an above V_{dd} voltage level word line is achieved without the use of double boot-strap circuits.